## VS-VSKCS409/150

**Vishay Semiconductors** 



## AAP Gen 7 (TO-240AA) Power Modules Schottky Rectifier, 400 A



### AAP Gen 7 (TO-240AA)

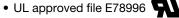
PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub> 400 A					
V <sub>R</sub>	150 V				
Package	AAP Gen 7 (TO-240AA)				
Circuit configuration Two diodes common cathode					

### **MECHANICAL DESCRIPTION**

The AAP Gen 7, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

### FEATURES

- 175 °C T<sub>J</sub> operation
- Low forward voltage drop
- High frequency operation
- Low thermal resistance



- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- High surge capability
- Easy mounting on heatsink

### **ELECTRICAL DESCRIPTION / APPLICATIONS**

The VS-VSKCS409/150 Schottky rectifier common cathode has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in high current switching power supplies, plating power supplies, UPS systems, converters, freewheeling diodes, welding, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	CHARACTERISTICS VALUES UNITS					
I <sub>F(AV)</sub>	Rectangular waveform	400	A				
V <sub>RRM</sub>		150	V				
I <sub>FSM</sub>	t <sub>p</sub> = 5 μs sine	20 000	А				
V <sub>F</sub>	200 A <sub>pk</sub> , T <sub>J</sub> = 125 °C	0.85	V				
TJ	Range	-55 to +175	°C				

VOLTAGE RATINGS						
PARAMETER SYMBOL VS-VSKCS409/150 UNITS						
Maximum DC reverse voltage	V <sub>R</sub>	150	V			
Maximum working peak reverse voltage	V <sub>RWM</sub>	150	v			



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ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDI	VALUES	UNITS	
Maximum average per module			50 % duty cycle at $T_{\rm C}$ = 105 °C	400		
forward current	per leg	I <sub>F(AV)</sub>	$50\%$ duty cycle at $T_{\rm C} = 105$ C	200		
Maximum peak one cycle non-repetitive surge current		<b>1</b>	5 $\mu s$ sine or 3 $\mu s$ rect. pulse	Following any rated load condition and with	20 000	A
		IFSM	10 ms sine or 6 ms rect. pulse	rated V <sub>RRM</sub> applied	2300	
Non-repetitive avalanche energ	у	E <sub>AS</sub>	T <sub>J</sub> = 25 °C, I <sub>AS</sub> = 1.8 A, L = 10 mH		15	mJ
Repetitive avalanche current		I <sub>AR</sub>	Current decaying linearly to zero in 1 $\mu$ s Frequency limited by T <sub>J</sub> maximum V <sub>A</sub> = 1.5 x V <sub>R</sub> typical		1	А

ELECTRICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CO	VALUES	UNITS			
		200 A	T.I = 25 °C	1.03	V		
Maximum forward voltage drop	V <sub>FM</sub>	400 A	1j=25 0	1.33			
maximum forward voltage drop		200 A	T.I = 125 °C	0.85			
		400 A	1j = 125 C	1.13			
Martinena in tarta a anno 1	I <sub>RM</sub>	$T_J = 25 \ ^{\circ}C$	$V_{\rm B}$ = Rated $V_{\rm B}$	6	mA		
Maximum reverse leakage current		T <sub>J</sub> = 125 °C	$v_{\rm R} = naleu v_{\rm R}$	85			
Maximum junction capacitance	CT	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz), 25 °C		6000	pF		
Typical series inductance	Ls	Measured lead to lead 5 mm from package body		5.0	nH		
Maximum voltage rate of change	dV/dt	Rated V <sub>R</sub>		10 000	V/µs		
Maximum RMS insulation voltage	V <sub>INS</sub>	50 Hz		3000 (1 min) 3600 (1 s)	V		

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C	
Maximum thermal resistance, junction to case per leg	' Bth IC		DC operation	0.32	°C/W	
Typical thermal resistance, case to heatsink per module		R <sub>thCS</sub>		0.1	0/11	
				75	g	
Approximate weight				2.7	oz.	
Mounting torque ± 10 %	to heatsink		A mounting compound is recommended and the torque should be rechecked after a period of 3 h to allow for the	4	Nm	
	busbar		spread of the compound.	3	INIT	
Case style			JEDEC®	TO-240AA co	ompatible	



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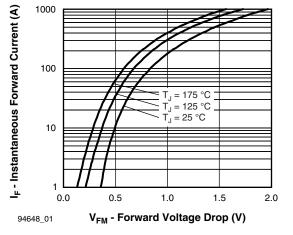
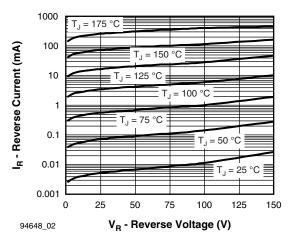


Fig. 1 - Maximum Forward Voltage Drop Characteristics (Per Leg)





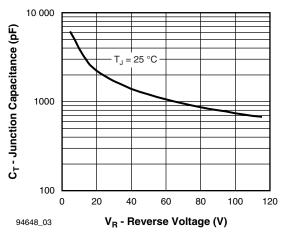


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

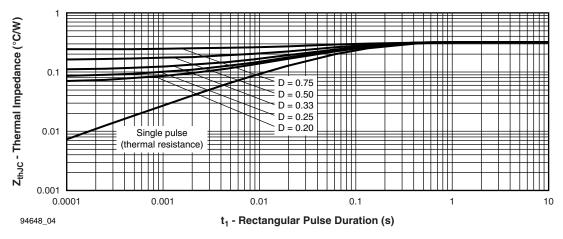
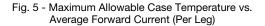


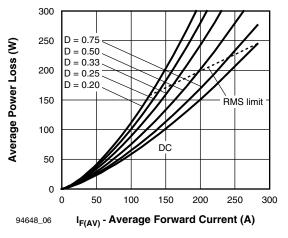
Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics (Per Diode)

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#### 180 Allowable Case Temperature (°C) 160 140 120 DC 100 80 60 Square wave (D = 0.50)40 80 % rated $\rm V_R$ applied 20 See note (1) 0 0 100 200 300 400 500 I<sub>F(AV)</sub> - Average Forward Current (A) 94648 05





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Fig. 6 - Forward Power Loss Characteristics (Per Leg)

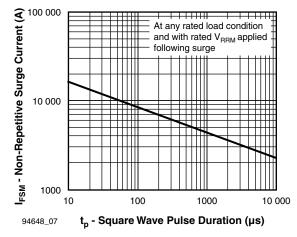


Fig. 7 - Maximum Non-Repetitive Surge Current

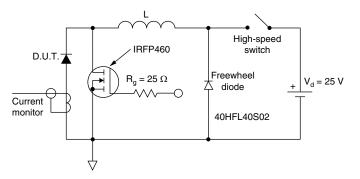


Fig. 8 - Unclamped Inductive Test Circuit

### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

Pd = forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 6); Pd<sub>REV</sub> = inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1} = 80$  % rated  $V_R$ 

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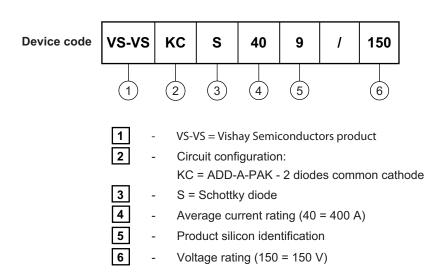
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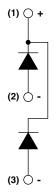




### **ORDERING INFORMATION TABLE**



### **CIRCUIT CONFIGURATION**



LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95369				

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## **ADD-A-PAK Generation VII - Diode**

### **DIMENSIONS** in millimeters (inches)





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